# Configurable 5.0 A ACOT Step Down Converter

The NCP6356B is a synchronous ACOT (Adaptive Constant On–time) buck converter optimized to supply the different sub systems of portable applications powered by one cell Li–Ion or three cell Alkaline/NiCd/NiMH batteries. The device is able to deliver up to 5.0 A, with programmable output voltage from 0.6 V to 1.4 V. Operation at up to 2.4 MHz switching frequency allows the use of small components. Synchronous rectification and automatic PFM Pseudo–PWM (PPWM) transitions improve overall solution efficiency. The NCP6356B is in a space saving, low profile 2.0 x 1.6 mm CSP–20 package.

#### **Features**

- Input Voltage Range from 2.5 V to 5.5 V: Battery and 5 V Rail Powered Applications
- Programmable Output Voltage: 0.6 V to 1.4 V in 6.25 mV Steps
- Up to 2.4 MHz Switching Frequency with On Chip Oscillator
- Uses 330 nH Inductor and at least 22 μF Capacitors for Optimized Footprint and Solution Thickness
- PFM/PPWM Operation for Optimum Efficiency
- Low 60 μA Quiescent Current
- I<sup>2</sup>C Control Interface with Interrupt and Dynamic Voltage Scaling Support
- Enable / VSEL Pins, Power Good / Interrupt Signaling
- Thermal Protections and Temperature Management
- Transient Load Helper: Share the Same Rail with Another Rail
- Small 2.0 x 1.6 mm / 0.4 mm Pitch CSP Package
- These are Pb-Free Devices

#### **Typical Applications**

- Smartphones
- Webtablets

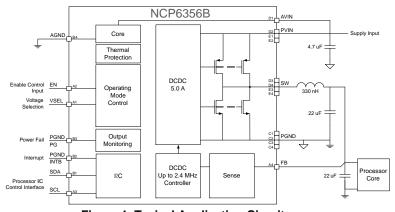


Figure 1. Typical Application Circuit



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#### MARKING DIAGRAM



= blank: production

= S: 0.95 V

= N: 1.20 V

= V: 1.00 V

= W: 0.80 V A = Assembly Location

WL = Wafer Lot

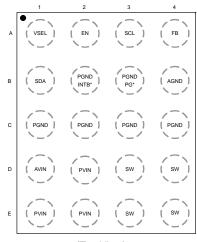
Y = Year

WW = Work Week

= Pb–Free Package

Pb–Free indicator, G or microdot (■), may or may not be present

#### **PIN OUT**



(Top View)
\*Optional

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 31 of this data sheet.

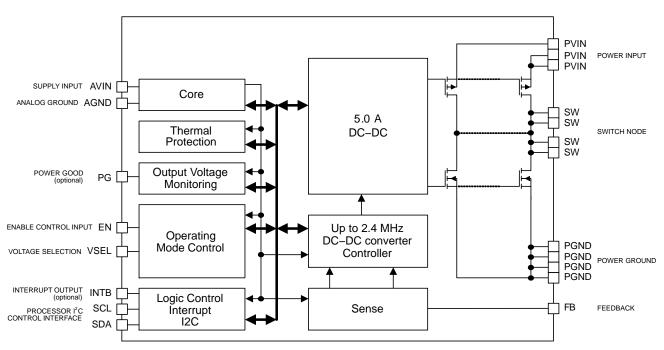


Figure 2. Simplified Block Diagram

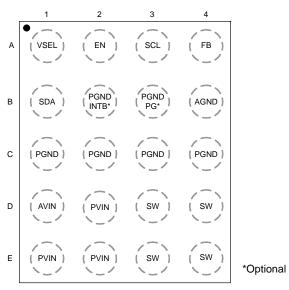


Figure 3. Pin Out (Top View)

### PIN FUNCTION DESCRIPTION

Pin	Name	Туре	Description
REFERENC	Ε	•	
D1	AVIN	Analog Input	Analog Supply. This pin is the device analog and digital supply. Can be connected directly to the VIN plane just next to the 4.7 $\mu$ F PVIN capacitor or to a dedicated 1.0 $\mu$ F ceramic capacitor. Must be equal to PVIN.
B4	AGND	Analog Ground	Analog Ground. Analog and digital modules ground. Must be connected to the system ground.
CONTROL	AND SERIAL IN	NTERFACE	
A2	EN	Digital Input	Enable Control. Active high will enable the part. There is an internal pull down resistor on this pin.
A1	VSEL	Digital Input	Output voltage / Mode Selection. The level determines which of two programmable configurations to utilize (operating mode / output voltage). There is an internal pull down resistor on this pin; can be left unconnected if not used.
А3	SCL	Digital Input	I <sup>2</sup> C interface <b>Clock</b> line. There is an internal pull down resistor on this pin; can be left unconnected if not used
B1	SDA	Digital Input/Output	I <sup>2</sup> C interface Bi–directional <b>Data</b> line. There is an internal pull down resistor on this pin; can be left unconnected if not used
ВЗ	PGND PG	Digital Output Analog Ground	Power Good open drain output. Must be connected to the ground plane if not used.
B2	PGND INTB	Digital Output Analog Ground	Interrupt open drain output. Must be connected to the ground plane if not used.
DC to DC C	ONVERTER		
D2, E1, E2	PVIN	Power Input	Switch Supply. These pins must be decoupled to ground by a 4.7 $\mu$ F ceramic capacitor. It should be placed as close as possible to these pins. All pins must be used with short thick connections. Must be equal to AVIN.
D3, D4, E3, E4	SW	Power Output	Switch Node. These pins supply drive power to the inductor. Typical application uses 0.33 $\mu$ H inductor; refer to application section for more information. All pins must be used with short thick connections.
C1, C2, C3, C4	PGND	Power Ground	Switch Ground. This pin is the power ground and carries the high switching current. High quality ground must be provided to prevent noise spikes. To avoid high–density current flow in a limited PCB track, a local ground plane that connects all PGND pins together is recommended. Analog and power grounds should only be connected together in one location with a trace.
A4	FB	Analog Input	<b>Feedback Voltage input.</b> Must be connected to the output capacitor positive terminal with a trace, not to a plane. This is the positive input to the error amplifier.

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Analog and power pins: AVIN, PVIN, SW, INTB, FB (Note 1)	V <sub>A</sub>	-0.3 to +6.0	V
I <sup>2</sup> C pins: SDA, SCL	V <sub>I2C</sub>	-0.3 to +6.0	V
Digital pins: EN, VSEL Input Voltage Input Current	V <sub>DG</sub> I <sub>DG</sub>	$-0.3$ to $V_A + 0.3 \le 6.0$	V mA
Human Body Model (HBM) ESD Rating (Note 2)	ESD HBM	2500	V
Charged Device Model (CDM) ESD Rating (Note 2)	ESD CDM	1250	V
Latch Up Current: (Note 3) Digital Pins All Other Pins	I <sub>LU</sub>	10 100	mA
Storage Temperature Range	T <sub>STG</sub>	-65 to +150	°C
Maximum Junction Temperature	T <sub>JMAX</sub>	-40 to +150	°C
Moisture Sensitivity (Note 4)	MSL	Level 1	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Refer to ELECTRICAL CHĂRACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for Safe Operating parameters.
- This device series contains ESD protection and passes the following ratings: Human Body Model (HBM) ± 2.5 kV per JEDEC standard: JESD22–A114. Charged Device Model (CDM) ± 1.25 V per JEDEC standard: JESD22–C101 Class IV
- 3. Latch up Current per JEDEC standard: JESD78 class II.
- 4. Moisture Sensitivity Level (MSL): 1 per IPC/JEDEC standard: J-STD-020A.

#### **OPERATING CONDITIONS**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$AV_{IN}$ , $PV_{IN}$	Power Supply	$AV_{IN} = PV_{IN}$	2.5		5.5	V
T <sub>A</sub>	Ambient Temperature Range		-40	25	+85	°C
$T_J$	Junction Temperature Range (Note 6)		-40	25	+125	°C
$R_{ heta JA}$	Thermal Resistance Junction to Ambient (Note 7)	CSP-20 on Demo-board	_	55	_	°C/W
P <sub>D</sub>	Power Dissipation Rating (Note 8)	T <sub>A</sub> ≤ 85°C	_	727	_	mW
P <sub>D</sub>	Power Dissipation Rating (Note 8)	T <sub>A</sub> = 65°C	_	1090	_	mW
L	Inductor for DC to DC converter (Note 5)		0.26	0.33	0.56	μΗ
Co	Output Capacitor for DC to DC Converter (Note 5)		15	_	150	μF
Cin	Input Capacitor for DC to DC Converter (Note 5)		4.5	_	_	μF

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

- 5. Including de-ratings (Refer to the Application Information section of this document for further details)
- 6. The thermal shutdown set to 150°C (typical) avoids potential irreversible damage on the device due to power dissipation.
- 7. The R<sub>0JA</sub> is dependent of the PCB heat dissipation. Board used to drive this data was a NCP6356BEVB board. It is a multilayer board with 1-once internal power and ground planes and 2-once copper traces on top and bottom of the board.
- 8. The maximum power dissipation (PD) is dependent by input voltage, maximum output current and external components selected.

$$R_{\theta JA} = \frac{125 - T_A}{P_D}$$

Cumbal	Dorometer	Conditions	Min	Trees	May	1154
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	RRENT: PINS AVIN – PVINX	1		T	ı	
I <sub>Q-PPWM</sub>	Operating quiescent current PPWM	DCDC active in Forced PPWM, no load	_	22	40	mA
I <sub>Q PFM</sub>	Operating quiescent current PFM	DCDC active in Auto mode no load – minimal switching	-	60	100	μΑ
I <sub>SLEEP</sub>	Product sleep mode current	EN high, DCDC off or EN low and $I^2$ C pull up $V_{IN} = 5.5 \text{ V}$	-	5	10	μΑ
I <sub>OFF</sub>	Product in off mode	EN, VSEL and Sleep_Mode low, No I <sup>2</sup> C pull up V <sub>IN</sub> = 5.5 V	-	0.8	3	μΑ
DC to DC C	ONVERTER					
PV <sub>IN</sub>	Input Voltage Range		2.5	_	5.5	V
I <sub>OUTMAX</sub>	Maximum Output Current	lpeak[10] = 00 (Note 11)	3.5	_	-	Α
		lpeak[10] = 01 (Note 11)	4.0	-	-	1
		lpeak[10] = 10 (Note 11)	4.5	_	-	
		lpeak[10] = 11 (Note 11)	5.0	_	_	1
$\Delta_{VOUT}$	Output Voltage DC Error Forced PPWM mode, V <sub>IN</sub> range, No load		-1.5	_	1.5	%
		Forced PPWM mode, V <sub>IN</sub> range, I <sub>OUT</sub> up to I <sub>OUTMAX</sub> (Note 11)	-2	_	2	
		Auto mode, V <sub>IN</sub> range, I <sub>OUT</sub> up to I <sub>OUTMAX</sub> (Note 11)	-3	_	2	
F <sub>SW</sub>	Switching Frequency		2.16	2.40	2.64	MHz
R <sub>ONHS</sub>	P-Channel MOSFET On Resistance	From PVIN to SW V <sub>IN</sub> = 5.0 V	_	22	32	mΩ
R <sub>ONLS</sub>	N-Channel MOSFET On Resistance	From SW to PGND V <sub>IN</sub> = 5.0 V	-	12	18	mΩ
I <sub>PK</sub>	Peak Inductor Current	Open loop – lpeak[10] = 00 (Note 11)	4.6	5.2	5.8	Α
		Open loop – lpeak[10] = 01 (Note 11)	5.2	5.8	6.4	1
		Open loop – lpeak[10] = 10 (Note 11)	5.6	6.2	6.8	
		Open loop – lpeak[10] = 11	6.2	6.8	7.4	1
DC <sub>LOAD</sub>	Load Regulation	I <sub>OUT</sub> from 0 A to I <sub>OUTMAX</sub> (Note 11) Forced PPWM mode	-	5	_	mV
DC <sub>LINE</sub>	Line Regulation	$2.5 \text{ V} \le \text{V}_{\text{IN}} \le 5.5 \text{ V} \text{ (Note 11)}$ Forced PPWM mode	_	6	-	mV
AC <sub>LOAD</sub>	Transient Load Response	$t_r = t_f = 100 \text{ ns}$ Load step 1.5 A (Note 11)	-	±20	-	mV
AC <sub>LINE</sub>	Transient Line Response	$t_{r}$ = $t_{f}$ = 10 $\mu s$ Line step 3.3 V / 3.9 V (Note 11)	_	±20	-	mV
D	Maximum Duty Cycle		-	100	-	%
t <sub>START</sub>	Turn on time	Time from EN transitions from Low to High to 90% of Output Voltage (DVS[10] = 00b)	-	100	130	μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>9.</sup> Refer to the Application Information section of this data sheet for more details.

<sup>10.</sup> Devices that use non-standard supply voltages which do not conform to the intent I<sup>2</sup>C bus system levels must relate their input levels to the V<sub>DD</sub> voltage to which the pull-up resistors R<sub>P</sub> are connected.

<sup>11.</sup> Guaranteed by design and characterized.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
DC to DC CC	ONVERTER					
R <sub>DISDCDC</sub>	DCDC Active Output Discharge	V <sub>OUT</sub> = 1.15 V	_	12	25	Ω
EN, VSEL						
$V_{IH}$	High input voltage		1.05	_	_	V
$V_{IL}$	Low input voltage		_	_	0.4	V
T <sub>FTR</sub>	Digital input X Filter	EN, VSEL rising and falling DBN_Time = 01 (Note 11)	0.5	-	4.5	μS
I <sub>PD</sub>	Digital input X Pull–Down (input bias current)	For EN and VSEL pins	-	0.05	1.00	μΑ
PG (Optiona	l)		•			•
$V_{PGL}$	Power Good Threshold	Falling edge as a percentage of nominal output voltage	86	90	94	%
V <sub>PGHYS</sub>	Power Good Hysteresis		0	3	5	%
T <sub>RT</sub>	Power Good Reaction Time for DCDC	Falling (Note 11) Rising (Note 11)	_ 3.5	3.5 -	- 14	μS
$V_{PGL}$	Power Good low output voltage	I <sub>PG</sub> = 5 mA	_	_	0.2	V
PG <sub>LK</sub>	Power Good leakage current	3.6 V at PG pin when power good valid	_	_	100	nA
$V_{PGH}$	Power Good high output voltage	Open drain	-	_	5.5	V
INTB (Option	nal)					
V <sub>INTBL</sub>	INTB low output voltage	I <sub>INT</sub> = 5 mA	0	_	0.2	V
V <sub>INTBH</sub>	INTB high output voltage	Open drain	-	-	5.5	V
INTB <sub>LK</sub>	INTB leakage current	3.6 V at INTB pin when INTB valid	-	-	100	nA
I <sup>2</sup> C						
V <sub>I2CIL</sub>	SCL, SDA low input voltage	SCL, SDA pin (Notes 10, 11)	_	_	0.4	V
V <sub>I2CIH</sub>	SCL high input voltage	SCL pin (Notes 10, 11)	1.6	_	_	V
	SDA high input voltage	SDA pin (Notes 10, 11)	1.2	_	_	
V <sub>I2COL</sub>	SDA low output voltage	I <sub>SINK</sub> = 3 mA (Note 11)	_	_	0.4	V
F <sub>SCL</sub>	I <sup>2</sup> C clock frequency	(Note 11)	_	_	3.4	MHz
TOTAL DEVI	CE					
$V_{UVLO}$	Under Voltage Lockout	V <sub>IN</sub> falling	_	_	2.5	V
$V_{UVLOH}$	Under Voltage Lockout Hysteresis	V <sub>IN</sub> rising	60	-	200	mV
T <sub>SD</sub>	Thermal Shut Down Protection		-	150	-	°C
T <sub>WARNING</sub>	Warning Rising Edge		-	135	-	°C
T <sub>PWTH</sub>	Pre – Warning Threshold	I <sup>2</sup> C default value	-	105	-	°C
T <sub>SDH</sub>	Thermal Shut Down Hysteresis		-	30	-	°C
T <sub>WARNINGH</sub>	Thermal warning Hysteresis		-	15	-	°C
T <sub>PWTH H</sub>	Thermal pre-warning Hysteresis		-	6	_	°C

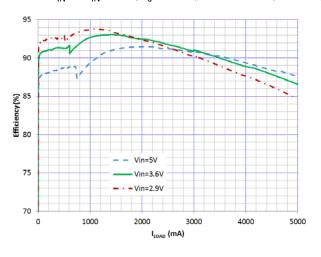
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<sup>9.</sup> Refer to the Application Information section of this data sheet for more details.

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<sup>11.</sup> Guaranteed by design and characterized.

 $\begin{tabular}{l} \textbf{TYPICAL OPERATING CHARACTERISTICS} \\ \textbf{AV}_{IN} = \textbf{PV}_{IN} = 3.6 \ \text{V}, \ \textbf{T}_J = +25 ^{\circ} \text{C}, \ \textbf{DCDC} = 1.15 \ \text{V}, \ \textbf{L} = 0.33 \ \mu \textbf{H} \ \textbf{DFE252012F} - \textbf{C}_{OUT} = 2 \ \textbf{x} \ 22 \ \mu \textbf{F} \ 0603, \ \textbf{C}_{IN} = 10 \ \mu \textbf{F} \ 0603 \ \textbf{C}_{IN} = 10 \ \mu \textbf{C$ 



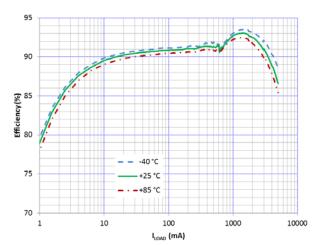


Figure 4. Efficiency vs.  $I_{LOAD}$  and  $V_{IN}$ V<sub>OUT</sub> = 1.39375 V, SPM5030 Inductor

Efficiency(%) Vin=5V 75 70

Figure 5. Efficiency vs. I<sub>LOAD</sub> and Temperature V<sub>OUT</sub> = 1.39375 V, SPM5030 Inductor

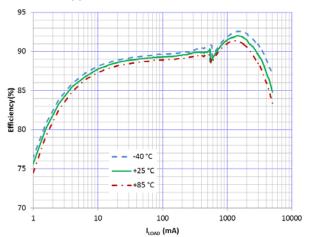


Figure 6. Efficiency vs.  $\rm I_{LOAD}$  and  $\rm V_{IN}$ V<sub>OUT</sub> = 1.15 V, SPM5030 Inductor

I<sub>LOAD</sub> (mA)

3000

4000

5000

2000

1000

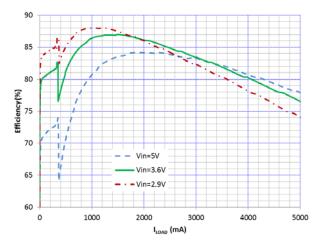


Figure 7. Efficiency vs.  $\rm I_{LOAD}$  and Temperature V<sub>OUT</sub> = 1.15 V, SPM5030 Inductor

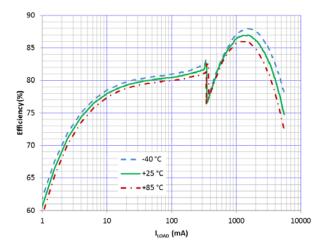
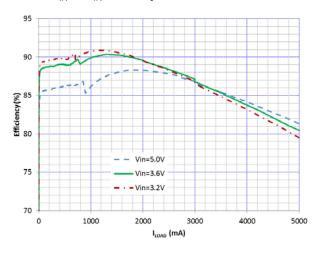


Figure 8. Efficiency vs.  $\rm I_{LOAD}$  and  $\rm V_{IN}$ V<sub>OUT</sub> = 0.60 V, SPM5030 Inductor

Figure 9. Efficiency vs.  $I_{\mbox{\scriptsize LOAD}}$  and Temperature V<sub>OUT</sub> = 0.60 V, SPM5030 Inductor

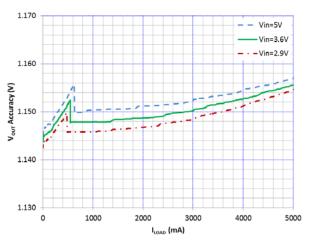
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95 90 Efficiency(%) 75 70 10 100 1000 10000 I<sub>LOAD</sub> (mA)

Figure 10. Efficiency vs.  $I_{\mbox{\scriptsize LOAD}}$  and  $V_{\mbox{\scriptsize IN}}$  $V_{OUT} = 1.15 V$ 

Figure 11. Efficiency vs.  $I_{\mbox{\scriptsize LOAD}}$  and Temperature  $V_{OUT} = 1.15 V$ 



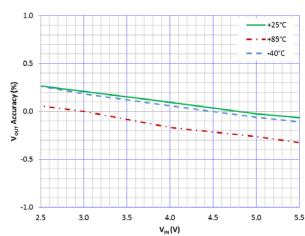
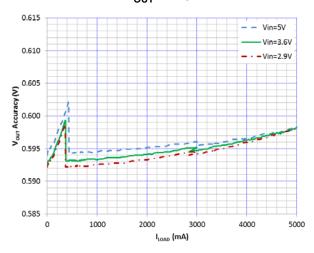


Figure 12.  $V_{OUT}$  Accuracy vs.  $I_{LOAD}$  and  $V_{IN}$  $V_{OUT} = 1.15 \text{ V}$ 

Figure 13. V<sub>OUT</sub> Accuracy vs. V<sub>IN</sub> and Temperature, V<sub>OUT</sub> = 1.15 V



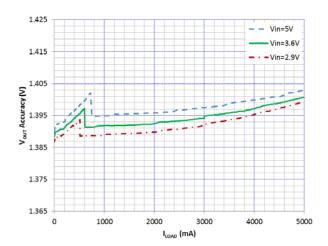
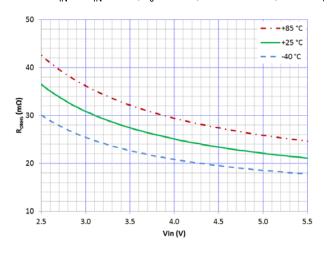


Figure 14.  $V_{OUT}$  Accuracy vs.  $I_{LOAD}$  and  $V_{IN}$  $V_{OUT} = 0.60 V$ 

Figure 15.  $V_{OUT}$  Accuracy vs.  $I_{LOAD}$  and  $V_{IN}$ V<sub>OUT</sub> = 1.39375 V

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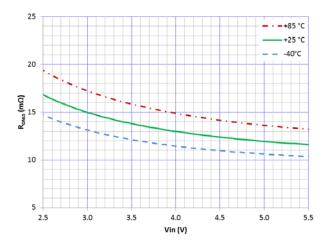
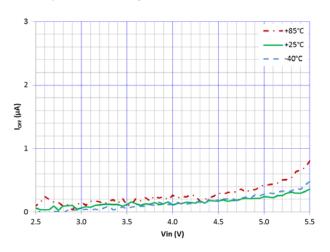


Figure 16. HSS  $R_{\text{ON}}$  vs.  $V_{\text{IN}}$  and Temperature

Figure 17. LSS  $R_{\mbox{\scriptsize ON}}$  vs.  $V_{\mbox{\scriptsize IN}}$  and Temperature



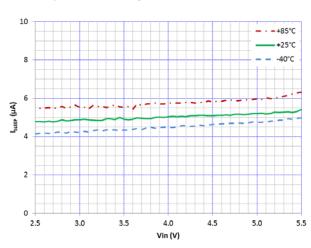
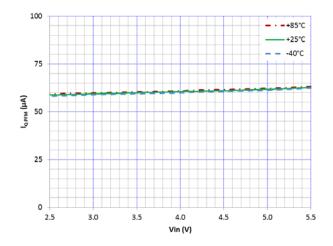


Figure 18. I<sub>OFF</sub> vs. V<sub>IN</sub> and Temperature

Figure 19. I<sub>SLEEP</sub> vs. V<sub>IN</sub> and Temperature



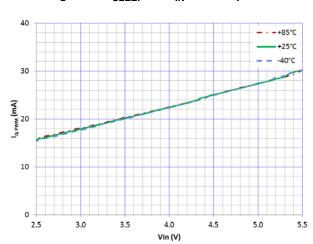
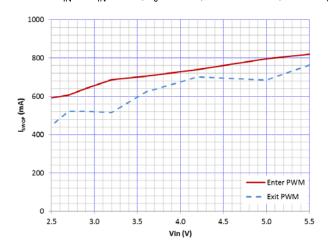


Figure 20.  $I_{\mbox{\scriptsize Q}\mbox{\scriptsize PFM}}$  vs.  $V_{\mbox{\scriptsize IN}}$  and Temperature

Figure 21.  $I_{\mbox{\scriptsize Q}\mbox{\scriptsize PPWM}}$  vs.  $V_{\mbox{\scriptsize IN}}$  and Temperature

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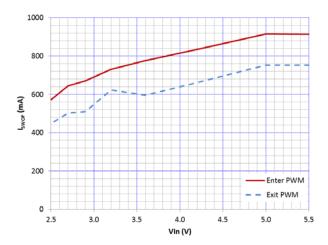
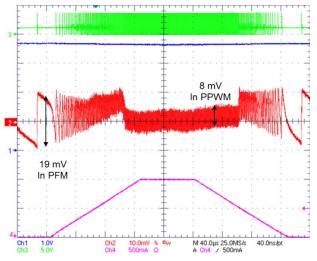


Figure 22. Switchover Point V<sub>OUT</sub> = 1.15 V

Figure 23. Switchover Point V<sub>OUT</sub> = 1.4 V



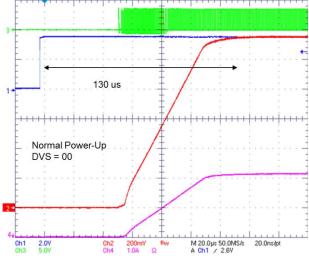


Figure 24. Ripple

Figure 25. Normal Power Up, V<sub>OUT</sub> = 1.15 V, DVS[1..0] = 00

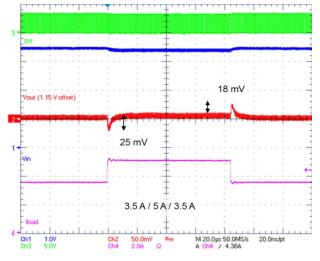
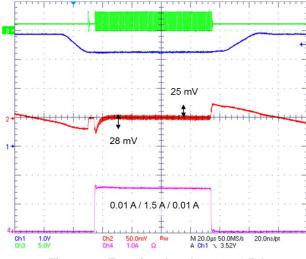


Figure 26. Transient Load 3.5 A to 5.0 A –  $V_{IN}$  = 3.2 V

#### TYPICAL OPERATING CHARACTERISTICS

 $AV_{IN} = PV_{IN} = 3.6 \text{ V}, T_J = +25 ^{\circ}\text{C}, DCDC = 1.15 \text{ V}, L = 0.33 ~\mu\text{H} \text{ DFE252012F} - C_{OUT} = 2 \times 22 ~\mu\text{F} \text{ } 0603, C_{IN} = 10 ~\mu\text{$ 



20mV

18 mV

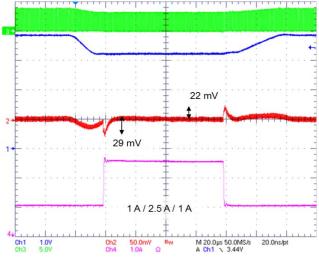
20mV

0.01 A / 1.5 A / 0.01 A

Ch1 1.0V Ch2 50.0mV Ew M 20.0 ps 50.0 Ms/s 20.0 ns.px
Ch3 5.0V Ch4 1.0A Q A Ch1 / 3.52V

Figure 27. Transient Load 0.01 to 1.5 A Transient Line 3.9 to 3.3 V – Auto Mode

Figure 28. Transient Load 0.01 to 1.5 A Transient Line 3.3 to 3.9 V – Auto Mode



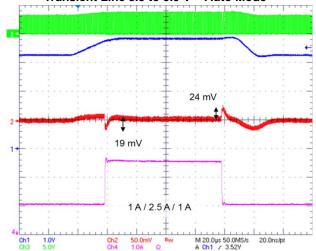
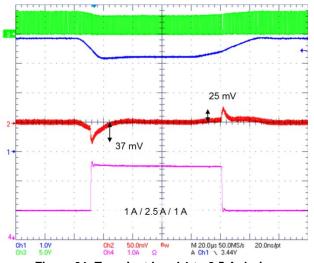


Figure 29. Transient Load 1 to 2.5 A Transient Line 3.9 to 3.3 V – Auto Mode

Figure 30. Transient Load 1 to 2.5 A Transient Line 3.3 to 3.9 V – Auto Mode



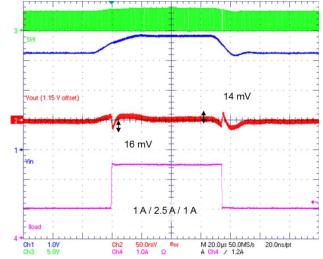


Figure 31. Transient Load 1 to 2.5 A during Transient Line 3.9 – 3.3 V Auto Mode

Figure 32. Transient Load 1 to 2.5 A during Transient Line 3.3 to 3.9 V – Auto Mode

#### DETAILED OPERATING DESCRIPTION

#### **Detailed Description**

The NCP6356B is voltage mode stand—alone DC to DC converter optimized to supply different sub systems of portable applications powered by one cell Li—Ion or three cells Alkaline/NiCd/NiMh. It can deliver up to 5 A at an I<sup>2</sup>C selectable voltage ranging from 0.6 V to 1.40 V. The switching frequency up to 2.4 MHz allows the use of small output filter components. Power Good indicator and Interrupt management are available. Operating modes, configuration, and output power can be easily selected either by using digital I/O pins or by programming a set of registers using an I<sup>2</sup>C compatible interface capable of operation up to 3.4 MHz. Default I<sup>2</sup>C settings are factory programmable.

#### **DC to DC Converter Operation**

The converter integrates both high side and low side (synchronous) switches. Neither external transistors nor diodes are required for NCP6356B operation. Feedback and compensation network are also fully integrated.

It uses the ACOT (Adaptive Constant On–Time) control scheme and can operate in two different modes: PFM and PPWM (Pseudo–PWM). The transition between modes can occur automatically or the switcher can be placed in forced PPWM mode by I<sup>2</sup>C programming (PPWMVSEL0 / PPWMVSEL1 bits of COMMAND register).

#### PPWM (Pseudo Pulse Width Modulation) Operating Mode

In medium and high load conditions, NCP6356B operates in PPWM mode to regulate the desired output voltage. In this mode, the inductor current is in CCM (Continuous Conduction Mode) and the ACOT guaranties a pseudo-fixed frequency with 10% accuracy. The internal N-MOSFET switch operates as a synchronous rectifier and is driven complementary to the P-MOSFET switch.

#### PFM (Pulse Frequency Modulation) Operating Mode

In order to save power and improve efficiency at low loads, the NCP6356B operates in PFM mode as the inductor current drops into DCM (Discontinuous Conduction Mode). The upper FET on–time is kept constant and the switching frequency becomes proportional to the loading current. As it does in PPWM mode, the internal N–MOSFET operates as a synchronous rectifier after each P–MOSFET on–pulse until there is no longer current in the coil.

When the load increases and the current in the inductor become continuous again, the controller automatically turns back to PPWM mode.

#### Forced PPWM

The NCP6356B can be programmed to only use PPWM and the transition to PFM can be disabled if so desired, thanks to the PPWMVSEL0 or PPWMVSEL1 I<sup>2</sup>C bits (COMMAND register).

#### **Output Stage**

NCP6356B is a 3.5 A to 5.0 A output current capable DC to DC converter with both high side and low side (synchronous) switches integrated.

#### **Inductor Peak Current Limitation / Short Protection**

During normal operation, peak current limitation monitors and limits the inductor current by checking the current in the P–MOSFET switch. When this current exceeds the Ipeak threshold, the P–MOSFET is immediately opened.

To protect again excessive load or short circuit, the number of consecutive Ipeak is counted. When the counter reaches 16, the DCDC is powered down during about 2 ms and the ISHORT interrupt is flagged. It will re–start following the REARM bit in the LIMCONF register:

- If REARM = 0, then NCP6356B does not re-start automatically, an EN pin toggle is required.
- If REARM = 1, NCP6356B re-starts automatically after the 2 ms with register values set prior the fault condition.

This current limitation is particularly useful to protect the inductor. The peak current can be set by writing IPEAK[1..0] bits in the LIMCONF register.

**Table 1. IPEAK VALUES** 

IPEAK[10]	Inductor Peak Current (A)
00	5.2 – for 3.5 output current
01	5.8 – for 4.0 output current
10	6.2 – for 4.5 output current
11	6.8 – for 5.0 output current

#### **Output Voltage**

The output voltage is set internally by an integrated resistor bridge and no extra components are needed to set the output voltage. Writing in the VoutVSEL0[6..0] bits of the PROGVSEL0 register or VoutVSEL1[6..0] bits of the PROGVSEL1 register will change the output voltage. The output voltage level can be programmed by 6.26 mV steps between 0.6 V to 1.39375 V. The VSEL pin and VSELGT bit will determine which register between PROGVSEL0 and PROGVSEL1 will set the output voltage.

- If VSELGT = 1 AND VSEL=0 → Output voltage is set by VoutVSEL0[6..0] bits (PROGVSEL0 register)
- Else → Output voltage is set by VoutVSEL1[6..0] bits (PROGVSEL1 register)

#### **Under Voltage Lock Out (UVLO)**

The NCP6356B core does not operate for voltages below the Under Voltage Lock Out (UVLO) level. Below the UVLO threshold, all internal circuitry (both analog and digital) is held in reset. The NCP6356B operation is guaranteed down to UVLO as the battery voltage is dropping off. To avoid erratic on / off behavior, a maximum 200 mV hysteresis is implemented. Restart is guaranteed at 2.7 V when the VBAT voltage is recovering or rising.

#### **Thermal Management**

#### Thermal Shut Down (TSD)

The thermal capability of the NCP6356B can be exceeded due to the step down converter output stage power level. A thermal protection circuitry with associated interrupt is therefore implemented to prevent the IC from damage. This protection circuitry is only activated when the core is in active mode (output voltage is turned on). During thermal shut down, output voltage is turned off. During thermal shut down, output voltage is turned off.

During thermal shutdown, the output voltage is turned off. When the NCP6356B returns from thermal shutdown, it can re–start in 2 different configurations depending on the REARM bit in the LIMCONF register (refer to the register description section):

If REARM = 0, the NCP6356B does not re-start after TSD. To restart, an EN pin toggle is required. If REARM = 1, the NCP6356B re-starts with register values set prior to thermal shutdown.

The thermal shut down threshold is set at 150°C (typical) and a 30°C hysteresis is implemented in order to avoid erratic on / off behavior. After a typical 150°C thermal shut down, the NCP6356B will resume to normal operation when the die temperature cools to 120°C.

#### Thermal Warnings

In addition to the TSD, the die temperature monitoring circuitry includes a thermal warning and thermal pre-warning sensor and interrupts. These sensors can inform the processor that the NCP6356B is close to its thermal shutdown and preventive measures to cool down die temperature can be taken by software.

The Warning threshold is set by hardware to 135°C typical. The Pre–Warning threshold is set by default to 105°C but it can be changed by setting the TPWTH[1..0] bits in the LIMCONF register.

#### **Active Output Discharge**

To make sure that no residual voltage remains in the power supply rail when disabled, an active discharge path can ground the NCP6356B output voltage. For maximum flexibility, this feature can be easily disabled or enabled with the DISCHG bit in the PGOOD register. By default the discharge path is enabled and is activated during the first 100 µs after battery insertion.

#### **Enabling**

The EN pin controls the NCP6356B start up. EN pin Low to High transition starts the power up sequencer. If EN is low, the DC to DC converter is turned off and device enters:

- Sleep Mode if Sleep\_Mode I<sup>2</sup>C bit is high or VSEL is high.
- Off Mode if Sleep Mode I<sup>2</sup>C bit and VSEL are low.

When EN pin is set to a high level, the DC to DC converter can be enabled / disabled by writing the ENVSEL0 or ENVSEL1 bit of the PROGVSEL0 and PROGVSEL1 registers:

- Enx I<sup>2</sup>C bit is high, the DC to DC converter is activated.
- Enx I<sup>2</sup>C is low, the DC to DC converter is turned off and the device enters in Sleep Mode.

A built in pull down resistor disables the device when this pin is left unconnected or not driven. EN pin activity does not generate any digital reset.

#### Power Up Sequence (PUS)

In order to power up the circuit, the input voltage AVIN has to rise above the VUVLO threshold. This triggers the internal core circuitry power up which is the "Wake Up Time" (including "Bias Time").

This delay is internal and cannot be bypassed. EN pin transition within this delay corresponds to the "Initial power up sequence" (IPUS):

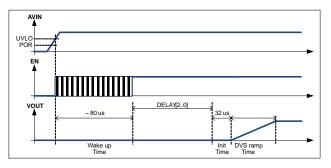


Figure 33. Initial Power Up Sequence

In addition a user programmable delay will also take place between the Wake Up Time and the Init time: The DELAY[2..0] bits of the TIME register will set this user programmable delay with a 2 ms resolution. With default delay of 0 ms, the NCP6356B IPUS takes roughly 100  $\mu$ s, and the DC to DC converter output voltage will be ready within 150  $\mu$ s.

The power up output voltage is defined by the VSEL state. NOTE: During the Wake Up time, the I<sup>2</sup>C interface is not active. Any I<sup>2</sup>C request to the IC during this time period will result in a NACK reply.

#### Normal, Quick and Fast Power Up Sequence

The previous description applies only when the EN transitions during the internal core circuitry power up (Wake up and calibration time). Otherwise 3 different cases are possible:

- Enabling the part by setting the EN pin from Off Mode will result in "Normal power up sequence" (NPUS, with DELAY;[2..0]).
- Enabling the part by setting the EN pin from Sleep Mode will result in "Quick power up sequence" (QPUS, with DELAY;[2..0]).
- Enabling the DC to DC converter, whereas EN is already high, either by setting the ENVSEL0 or ENVSEL1 bits or by VSEL pin transition will results in

"Fast power up sequence" (FPUS, without DELAY[2..0]).

Sleep mode is when VSEL is high and EN low, or when Sleep\_Mode I<sup>2</sup>C bit is set and EN is low, or finally when DC to DC converter is off and EN high.

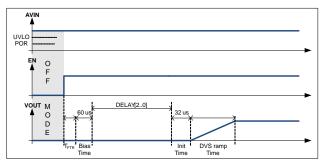


Figure 34. Normal Power Up Sequence

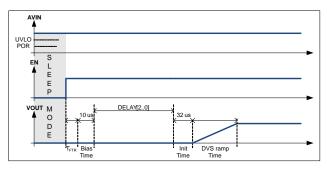


Figure 35. Quick Power Up Sequence

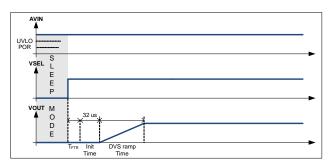


Figure 36. Fast Power Up Sequence

In addition the delay set in DELAY[2..0] bits in TIME register will apply only for the EN pins turn ON sequence (NPUS and QPUS).

The power up output voltage is defined by VSEL state.

#### DC to DC Converter Shut Down

When shutting down the device, no shut down sequence is required. The output voltage is disabled and, depending on the DISCHG bit state of the PGOOD register, the output may be discharged.

DC to DC converter shutdown is initiated by either grounding the EN pin (Hardware Shutdown) or, depending on the VSEL internal signal level, by clearing the ENVSEL0 or ENVSEL1 bits (Software shutdown) in the PROGVSEL0 or PROGVSEL1 registers.

In hardware shutdown (EN = 0), the internal core is still active and  $I^2C$  accessible.

The internal core of the NCP6356B shuts down when AVIN falls below UVLO

#### **Dynamic Voltage Scaling (DVS)**

The NCP6356B supports dynamic voltage scaling (DVS) allowing the output voltage to be reprogrammed via I<sup>2</sup>C commands and provides the different voltages required by the processor. The change between set points is managed in a smooth fashion without disturbing the operation of the processor.

When programming a higher voltage, the output raises with controlled dV/dt defined by DVS[1..0] bits in the TIME register. When programming a lower voltage the output voltage will decrease accordingly. The DVS step is fixed and the speed is programmable.

The DVS sequence is automatically initiated by changing the output voltage settings. There are two ways to change these settings:

- Directly change the active setting register value (VoutVSEL0[6..0] of the PROGVSEL0 register or VoutVSEL1[6..0] of the PROGVSEL1 register) via an I<sup>2</sup>C command
- Change the VSEL internal signal level by toggling the VSEL pin.

The second method eliminates the I<sup>2</sup>C latency and is therefore faster.

The DVS transition mode can be changed with the DVSMODE bit in the COMMAND register:

• In forced PPWM mode when accurate output voltage control is needed. Rise and fall time are controlled with the DVS[1..0] bits.

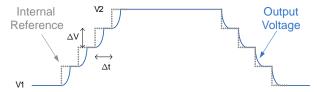


Figure 37. DVS in Forced PPWM Mode Diagram

 In Auto mode when the output voltage must not be discharged. Rise time is controlled by the DVS[1..0], and fall time depends on the load and cannot be faster than the DVS[1..0] settings.

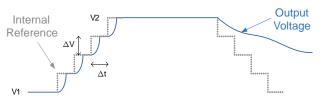


Figure 38. DVS in Auto Mode Diagram

#### **Digital IO Settings**

#### **VSEL Pin**

By changing the VSEL pin levels, the user has a latency free way to change the NCP6356B configuration: the operating mode, the output voltage as well as the enable (see Table 2).

**Table 2. VSEL PIN PARAMETERS** 

Parameter VSEL	REGISTER	REGISTER
Pin Can Set	VSEL = LOW	VSEL = HIGH
ENABLE	ENVSEL0 PROGVSEL0[7]	ENVSEL1 PROGVSEL1[7]
VOUT	VoutVSEL0[60]	VoutVSEL1[60]
OPERATING MODE	PWMVSEL0	PWMVSEL1
(Auto / PPWM Forced)	COMMAND[7]	COMMAND[6]

VSEL pin action can be masked by writing 0 to the VSELGT bit in the COMMAND register. In that case the I<sup>2</sup>C bit corresponding to VSEL high will be taken into account.

#### **EN Pin**

The EN pin can be gated by writing the ENVSEL0 or ENVSEL1 bits of the PROGVSEL0 and PROGVSEL1 registers, depending on which register is activated by the VSEL internal signal.

# Power Good Pin (Optional)

To indicate the output voltage level is established, a power good signal is available.

The power good signal is low when the DC to DC converter is off. Once the output voltage reaches 95% of the expected output level, the power good logic signal becomes high and the open drain output becomes high impedance.

During a positive DVS sequence when the target voltage is higher than the initial voltage, the Power Good logic signal will be set low during the output voltage ramping and will transition to high once the output voltage reaches 95% of the target voltage. When the target voltage is lower than the initial voltage, the Power Good pin will remain at a high level during the transition.

The Power Good signal during normal operation can be disabled by clearing the PGDCDC bit in the PGOOD register.

The Power Good operation during DVS can be controlled by setting / clearing the PGDVS bit in the PGOOD register.

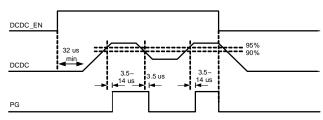


Figure 39. Power Good Signal

#### Power Good Delay

In order to generate a Reset signal, a delay can be programmed between when the output voltage gets 95% of

its final value and when the Power Good pin is released to a high level.

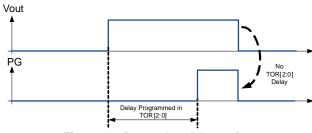


Figure 40. Power Good Operation

#### Interrupt Pin (Optional)

The interrupt controller continuously monitors internal interrupt sources, generating an interrupt signal when a system status change is detected (dual edge monitoring).

**Table 3. INTERRUPT SOURCES** 

Interrupt Name	Description
TSD	Thermal Shut Down
TWARN	Thermal Warning
TPREW	Thermal Pre Warning
UVLO	Under Voltage Lock Out
IDCDC	DC to DC converter Current Over / below limit
ISHORT	DC to DC converter Short–Circuit Protection
PG	Power Good

Individual bits generating interrupts will be set to 1 in the INT\_ACK register (I<sup>2</sup>C read only registers), indicating the interrupt source. INT\_ACK register is automatically reset by an I<sup>2</sup>C read. The INT\_SEN register (read only register) contains real time indicators of interrupt sources.

All interrupt sources can be masked by writing in register INT\_MSK. Masked sources will never generate an interrupt request on the INTB pin.

The INTB pin is an open drain output. A non-masked interrupt request will result in the INTB pin being driven low.

When the host reads the INT\_ACK registers the INTB pin is released to high impedance and the interrupt register INT ACK is cleared.

Figure 41 is an example of an UVLO event of the INTB pin with INT\_SEN/INT\_MSK/INT\_ACK and an I<sup>2</sup>C read access behavior.

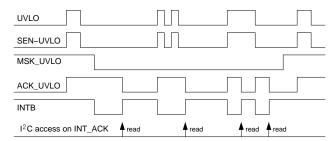


Figure 41. Interrupt Operation Example

# Configurations

Default output voltages, enables, DCDC modes, current limit and other parameters can be factory programmed upon request. Below are the pre-defined default configurations:

**Table 4. NCP6356B CONFIGURATION** 

Configuration	5.0 A NCP6356B	4.0 A NCP6356BS	4.0 A NCP6356BSN	5.0 A NCP6356BV	5.0 A NCP6356BW
Default I <sup>2</sup> C address PID product identification RID revision identification FID feature identification	0x14 19h Metal 00h	0x1C 19h Metal 08h	0x1C 19h Metal 09h	0x14 19h Metal 04h	0x14 19h Metal 05h
Default VOUT – VSEL=1	1.15 V	0.95 V	1.20 V	1.00 V	0.80 V
Default VOUT - VSEL=0	1.15 V	0.95 V	1.20 V	1.00 V	0.65 V
Default Enable – VSEL=1	ON	ON	ON	ON	ON
Default Enable – VSEL=0	ON	ON	ON	ON	ON
Default MODE – VSEL=1	Forced PPWM	Auto mode	Auto mode	Forced PPWM	Forced PPWM
Default MODE – VSEL=0	Auto mode	Auto mode	Auto mode	Forced PPWM	Forced PPWM
Default IPEAK	6.8 A	5.8 A	5.8 A	6.8 A	6.8 A
OPN	NCP6356BFCCT 1G	NCP6356BSFCC T1G	NCP6356BSNFC CT1G	NCP6356BVFCC T1G	NCP6356BWFC CT1G
Marking	6356B	6356BS	6356BN	6356BV	6356BW

#### I<sup>2</sup>C Compatible Interface

The NCP6356B can support a subset of the I<sup>2</sup>C protocol as detailed below.

#### I<sup>2</sup>C Communication Description

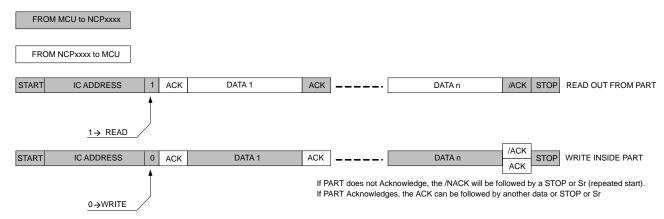


Figure 42. General Protocol Description

The first byte transmitted is the Chip address (with the LSB bit set to 1 for a read operation, or set to 0 for a Write operation). The following data will be:

- During a Write operation, the register address (@REG) is written in followed by the data. The writing process is auto-incremental, so the first data will be written in @REG, the contents of @REG are incremented and the next data byte is placed in the location pointed to by @REG + 1 ..., etc.
- During a Read operation, the NCP6356B will output the data from the last register that has been accessed by the last write operation. Like the writing process, the reading process is auto-incremental.

#### **Read Sequence**

The Master will first make a "Pseudo Write" transaction with no data to set the internal address register. Then, a stop then start or a Repeated Start will initiate the read transaction from the register address the initial write transaction has pointed to:

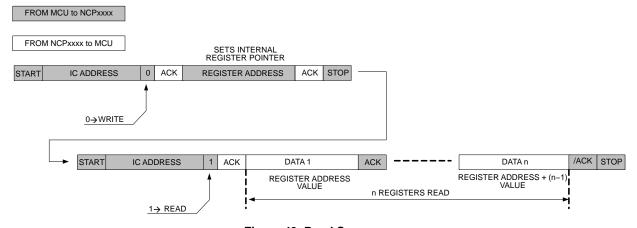


Figure 43. Read Sequence

The first WRITE sequence will set the internal pointer to the register that is selected. Then the read transaction will start at the address the write transaction has initiated.

#### **Write Sequence**

Write operation will be achieved by only one transaction. After chip address, the REG address has to be set, then following data will be the data we want to write in REG, REG + 1, REG + 2, ..., REG + n.

# Write n Registers:

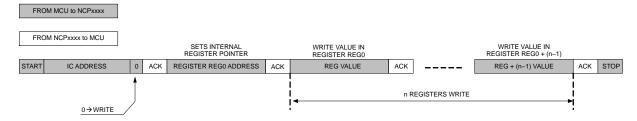


Figure 44. Write Sequence

#### Write then Read Sequence

#### With Stop Then Start

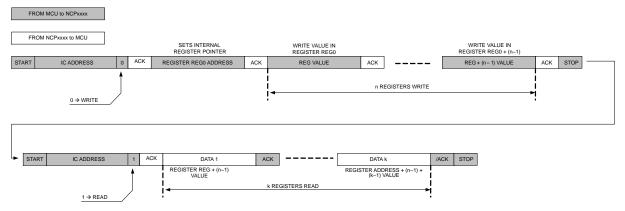


Figure 45. Write Followed by Read Transaction

### I<sup>2</sup>C Address

The NCP6356B has 8 available  $I^2C$  addresses selectable by factory settings (ADD0 to ADD7). Different address settings can be generated upon request to ON Semiconductor. See Table 4 (NCP6356B Configuration) for the default  $I^2C$  address.

Table 5. I<sup>2</sup>C ADDRESS

I <sup>2</sup> C Address	Hex	A7	A6	A5	A4	А3	A2	A1	A0
ADD0	W 0x20 R 0x21	0	0	1	0	0	0	0	R/W
	Add		•	•	0x10	•	•	•	-
ADD1	W 0x28 R 0x29	0	0	1	0	1	0	0	R/W
	Add		•	•	0x14	•	•	•	-
ADD2	W 0x30 R 0x31	0	0	1	1	0	0	0	R/W
	Add				0x18				-
ADD3	W 0x38 R 0x39	0	0	1	1	1	0	0	R/W
	Add		•	•	0x1C	•		•	-
ADD4	W 0xC0 R 0xC1	1	1	0	0	0	0	0	R/W
	Add				0x60	-			_
ADD5	W 0xC8 R 0xC9	1	1	0	0	1	0	0	R/W
	Add		•	•	0x64	•		•	-
ADD6	W 0xD0 R 0xD1	1	1	0	1	0	0	0	R/W
	Add		•	•	0x68	•		•	-
ADD7	W 0xD8 R 0xD9	1	1	0	1	1	0	0	R/W
	Add		-	-	0x6C	-	-	-	-

# **Register Map**

The tables below describe the I<sup>2</sup>C registers.

Registers / bits Operations:

R Read only register
RC Read then Clear
RW Read and Write register

Reserved Address is reserved and register / bit is not physically designed Spare Address is reserved and register / bit is physically designed

# Table 6. I<sup>2</sup>C REGISTERS MAP CONFIGURATION (NCP6356B)

Add.	Register Name	Туре	Def.	Function
00h	INT_ACK	RC	00h	Interrupt register
01h	INT_SEN	R	00h	Sense register (real time status)
02h	INT_MSK	RW	FFh	Mask register to enable or disable interrupt sources (trim)
03h	PID	R	19h	Product Identification
04h	RID	R	Metal	Revision Identification
05h	FID	R	00h	Features Identification (trim)
06h to 0Fh	-	-	_	Reserved for future use
10h	PROGVSEL1	RW	D8h	Output voltage settings and EN for VSEL pin = High (trim)
11h	PROGVSEL0	RW	D8h	Output voltage settings and EN for VSEL pin = Low (trim)
12h	PGOOD	RW	10h	Power good and active discharge settings (trim)
13h	TIME	RW	09h	Enabling and DVS timings (trim)
14h	COMMAND	RW	43h	Enabling and Operating mode Command register (trim)
15h	-	-	_	Reserved for future use
16h	LIMCONF	RW	E3h	Reset and limit configuration register (trim)
17h to 1Fh	-	-	-	Reserved for future use
20h to FFh	-	-	-	Reserved. Test Registers

# Table 7. I<sup>2</sup>C REGISTERS MAP CONFIGURATION (NCP6356BS)

Add.	Register Name	Type	Def.	Function
00h	INT_ACK	RC	00h	Interrupt register
01h	INT_SEN	R	00h	Sense register (real time status)
02h	INT_MSK	RW	FFh	Mask register to enable or disable interrupt sources (trim)
03h	PID	R	19h	Product Identification
04h	RID	R	Metal	Revision Identification
05h	FID	R	08h	Features Identification (trim)
06h to 0Fh	-	_	_	Reserved for future use
10h	PROGVSEL1	RW	B8h	Output voltage settings and EN for VSEL pin = High (trim)
11h	PROGVSEL0	RW	B8h	Output voltage settings and EN for VSEL pin = Low (trim)
12h	PGOOD	RW	10h	Power good and active discharge settings (trim)
13h	TIME	RW	01h	Enabling and DVS timings (trim)
14h	COMMAND	RW	03h	Enabling and Operating mode Command register (trim)
15h	_	_	-	Reserved for future use
16h	LIMCONF	RW	63h	Reset and limit configuration register (trim)
17h to 1Fh	-	_	-	Reserved for future use
20h to FFh	_	_	-	Reserved. Test Registers

Table 8. I<sup>2</sup>C REGISTERS MAP CONFIGURATION (NCP6356BSN)

Add.	Register Name	Туре	Def.	Function
00h	INT_ACK	RC	00h	Interrupt register
01h	INT_SEN	R	00h	Sense register (real time status)
02h	INT_MSK	RW	FFh	Mask register to enable or disable interrupt sources (trim)
03h	PID	R	19h	Product Identification
04h	RID	R	Metal	Revision Identification
05h	FID	R	09h	Features Identification (trim)
06h to 0Fh	-	_	-	Reserved for future use
10h	PROGVSEL1	RW	E0h	Output voltage settings and EN for VSEL pin = High (trim)
11h	PROGVSEL0	RW	E0h	Output voltage settings and EN for VSEL pin = Low (trim)
12h	PGOOD	RW	10h	Power good and active discharge settings (trim)
13h	TIME	RW	01h	Enabling and DVS timings (trim)
14h	COMMAND	RW	03h	Enabling and Operating mode Command register (trim)
15h	-	_	-	Reserved for future use
16h	LIMCONF	RW	63h	Reset and limit configuration register (trim)
17h to 1Fh	-	_	-	Reserved for future use
20h to FFh	-	_	_	Reserved. Test Registers

# Table 9. I<sup>2</sup>C REGISTERS MAP CONFIGURATION (NCP6356BV)

Add.	Register Name	Туре	Def.	Function
00h	INT_ACK	RC	00h	Interrupt register
01h	INT_SEN	R	00h	Sense register (real time status)
02h	INT_MSK	RW	FFh	Mask register to enable or disable interrupt sources (trim)
03h	PID	R	19h	Product Identification
04h	RID	R	Metal	Revision Identification
05h	FID	R	04h	Features Identification (trim)
06h to 0Fh	-	-	-	Reserved for future use
10h	PROGVSEL1	RW	C0h	Output voltage settings and EN for VSEL pin = High (trim)
11h	PROGVSEL0	RW	C0h	Output voltage settings and EN for VSEL pin = Low (trim)
12h	PGOOD	RW	10h	Power good and active discharge settings (trim)
13h	TIME	RW	09h	Enabling and DVS timings (trim)
14h	COMMAND	RW	C3h	Enabling and Operating mode Command register (trim)
15h	-	-	-	Reserved for future use
16h	LIMCONF	RW	E3h	Reset and limit configuration register (trim)
17h to 1Fh	-	-	-	Reserved for future use
20h to FFh	-	-	-	Reserved. Test Registers

# Table 10. I<sup>2</sup>C REGISTERS MAP CONFIGURATION (NCP6356BW)

Add.	Register Name	Туре	Def.	Function		
00h	INT_ACK	RC	00h	Interrupt register		
01h	INT_SEN	R	00h	Sense register (real time status)		
02h	INT_MSK	RW	FFh	Mask register to enable or disable interrupt sources (trim)		
03h	PID	R	19h	Product Identification		
04h	RID	R	Metal	Revision Identification		
05h	FID	R	05h	Features Identification (trim)		
06h to 0Fh	-	-	_	Reserved for future use		
10h	PROGVSEL1	RW	A0h	Output voltage settings and EN for VSEL pin = High (trim)		
11h	PROGVSEL0	RW	88h	Output voltage settings and EN for VSEL pin = Low (trim)		
12h	PGOOD	RW	10h	Power good and active discharge settings (trim)		
13h	TIME	RW	09h	Enabling and DVS timings (trim)		
14h	COMMAND	RW	C3h	Enabling and Operating mode Command register (trim)		
15h	-	-	_	Reserved for future use		
16h	LIMCONF	RW	E3h	Reset and limit configuration register (trim)		
17h to 1Fh	-	_	_	Reserved for future use		
20h to FFh	-	-	_	Reserved. Test Registers		

# **Registers Description**

# Table 11. INTERRUPT ACKNOWLEDGE REGISTER

Name: INTA	CK				Address: 00h					
Type: RC					Default: 00000000b (00h)					
Trigger: Dua	I Edge [D7D	0]								
D7	D6		D5 D4 D3 D2 D1							
ACK_TSD	ACK_TWA	RN	RN ACK_TPREW Spare = 0 ACK_ISHORT ACK_UVLO ACK_IDCDC ACK_PG							
Bi	t				Bit Descrip	tion				
ACK_	PG_	0: Cl	Power Good Sense Acknowledgement 0: Cleared 1: DCDC Power Good Event detected							
ACK_IDCDC		DCDC Over Current Sense Acknowledgement 0: Cleared 1: DCDC Over Current Event detected								
ACK_L	JVLO	0: Cl	er Voltage Sense A eared nder Voltage Event	•	ı					
ACK_IS	HORT	0: Cl	C Short–Circuit Pr eared CDC Short circuit p		ŭ					
ACK_TI	PREW	0: Cl	mal Pre Warning S eared ermal Pre Warning		gement					
ACK_T\	WARN	Thermal Warning Sense Acknowledgement 0: Cleared 1: Thermal Warning Event detected								
ACK_	TSD	0: Cl	mal Shutdown Ser eared ermal Shutdown E	· ·	ment					

# Table 12. INTERRUPT SENSE REGISTER

Name: INTS	EN				Address: 01h					
Type: R					Default: 00000000b (00h)					
Trigger: N/A	1									
D7	D6		D5	D4	D3	D2	D1	D0		
SEN_TSD	SEN_TWA	RN SEN_TPREW Spare = 0 SEN_ISHORT SEN_UVLO SEN_IDCDC SEN_PG								
Bi	it				Bit Descrip	tion				
SEN_	_PG	0: DC	er Good Sense CDC Output Voltag CDC Output Voltag		range					
SEN_IDCDC		DCDC over current sense 0: DCDC output current is below limit 1: DCDC output current is over limit								
SEN_l	JVLO	0: Inp	r Voltage Sense out Voltage higher out Voltage lower t							
SEN_IS	SHORT	0: Sh	C Short-Circuit Pr ort-Circuit detecte ort-Circuit not det	ed not detected						
SEN_T	PREW	0: Jui	mal Pre Warning S nction temperature nction temperature	below thermal p						
SEN _T	WARN	Thermal Warning Sense 0: Junction temperature below thermal warning limit 1: Junction temperature over thermal warning limit								
SEN_	TSD	0: Ju	mal Shutdown Ser nction temperature nction temperature	below thermal s						

#### **Table 13. INTERRUPT MASK REGISTER**

Name: INTM	SK				Address: 02h					
Type: RW					Default: See Register map					
Trigger: N/A										
D7	D6		D5	D4	D3	D2	D1	D0		
MSK_TSD	MSK_TWA	RΝ	MSK_TPREW	Spare = 1	MSK_ISHORT	MSK_UVLO	MSK_IDCDC	MASK_PG		
Bit	t				Bit Descript	ion				
MSK_	_PG	Power Good interrupt source mask 0: Interrupt is Enabled 1: Interrupt is Masked								
MSK_I	OCDC	DCDC over current interrupt source mask 0: Interrupt is Enabled 1: Interrupt is Masked								
MSK_L	JVLO	0: Int	er Voltage interrupt s terrupt is Enabled terrupt is Masked	ource mask						
MSK_IS	HORT	0: Int	C Short-Circuit Proterrupt is Enabled terrupt is Masked	ection source r	nask					
MSK_TF	PREW	0: Int	mal Pre Warning inte terrupt is Enabled terrupt is Masked	errupt source m	nask					
MSK_T\	WARN	0: Int	Thermal Warning interrupt source mask 0: Interrupt is Enabled 1: Interrupt is Masked							
MSK_	TSD	0: Int	mal Shutdown interr terrupt is Enabled terrupt is Masked	upt source mas	sk					

### Table 14. PRODUCT ID REGISTER

Name: PID		Address: 03h					
Type: R				Default: 00011001b (19h)			
Trigger: N/A				Reset on N/A			
D7	D6	D5	D4	D3	D2	D1	D0
PID_7	PID_7 PID_6 PID_5 PID_4				PID_2	PID_1	PID_0

### Table 15. REVISION ID REGISTER

Name: RID			Address: 04	Address: 04h				
Type: R			Default: Met	Default: Metal				
Trigger: N/A								
D7	D6	D5	D4	D3	D2	D1	D0	
RID_7	RID_6	RID_5	RID_4	RID_3	RID_2	RID_1	RID_0	
Bit				Bit Descri	ption			
RID[70] Revision Identification 0000000X: Prototype Silicon 00000010: Production								

### Table 16. FEATURE ID REGISTER

Name: FID				Address: 05h					
Type: R				Default: See F	Default: See Register map				
Trigger: N/A									
D7	D6	D6 D5 D4			D2	D1	D0		
Spare	Spare	Spare	Spare	FID_3	FID_2	FID_1	FID_0		
Bit		•	•	Bit Descri	ption	•	•		
FID[3	0]	Feature Identification See Table 4: NCP635	Feature Identification See Table 4: NCP6356B Configuration						

# Table 17. DC TO DC VOLTAGE PROG (VSEL = 1) REGISTER

Name: PROGVSEL	.1			Address: 10h	Address: 10h				
Type: RW			Default: See R	egister map					
Trigger: N/A									
D7	D6	D5	D4	D3	D2	D1	D0		
ENVSEL1		VoutVSEL1[60]							
Bit				Bit Description	on				
VoutVSEL1[60]	COMMAND	D.D0, or when VS	SEL pin function i	when VSEL pin = s disabled in regis nV (steps of 6.25 r	ster COMMAND.I		ed in register		
ENVSEL1	EN Pin Gati 0: Disabled 1: Enabled	ng for VSEL inte	ernal signal = Hig	h					

# Table 18. DC TO DC VOLTAGE PROG (VSEL = 0) REGISTER

Name: PROGVSE	L0			Address: 11h				
Type: RW			Default: See Register map					
Trigger: N/A								
D7	D6	D6 D5 D4 D3 D2 D1						
ENVSEL0		VoutVSEL0[60]						
Bit				Bit Description				
VoutVSEL0[60]	COMMAND.D0			en VSEL pin = 0 a (steps of 6.25 mV)	•	ction is enabled in	register	
ENVSEL0	EN Pin Gating f 0: Disabled 1: Enabled							

### Table 19. POWER GOOD REGISTER

Name: PGOO	D			Address: 1	2h					
Type: RW				Default: See Register map						
Trigger: N/A										
D7	D6	D5	D4	D3	D2	D1	D0			
Spare = 0	Spare = 0	Spare = 0         Spare = 0         DISCHG         TOR[10]         PGDVS         PGDCDC								
Bit	Bit Description									
PGDCDC	Power Good Enabling 0 = Disabled 1 = Enabled									
PGDVS	Power Good Active C 0 = Disabled 1 = Enabled	On DVS								
TOR[10]	Time out Reset settin 00 = 0 ms 01 = 8 ms 10 = 32 ms 11 = 64 ms	01 = 8 ms 10 = 32 ms								
DISCHG	Active discharge bit E 0 = Discharge path di 1 = Discharge path e	isabled								

### **Table 20. TIMING REGISTER**

Name: TIME				Address: 13h				
Type: RW				Default: See Register map				
Trigger: N/A								
D7 D6 D5		D4	D3	D2	D1	D0		
DELAY[20]			DVS	S[10] Spare = 0 DBN_Time		Time[10]		
Bit				Bit Description				
DBN_Time[10]		EN and VSEL debounce time $00 = \text{No debounce}$ $01 = 1-2 \ \mu\text{s}$ $10 = 2-3 \ \mu\text{s}$ $11 = 3-4 \ \mu\text{s}$						
01 = 6.25 mV s 10 = 6.25 mV s		DVS Speed 00 = 6.25 mV step / 0 01 = 6.25 mV step / 0 10 = 6.25 mV step / 1 11 = 6.25 mV step / 2	.666 μs .333 μs					
DELAY[20] Delay applied upon enabling (ms) 000b = 0 ms - 111b = 14 ms (Steps o		2 ms)						

### **Table 21. COMMAND REGISTER**

Name: COMMAND				Address: 14h					
Type: RW				Default: See Register map					
Trigger: N/A									
D7	D7 D6		D5	D4	D3	D2	D1	D0	
PPWMVSEL0	PPWMV	SEL1	DVSMODE	Sleep_Mode	Spare = 0	Spare = 0	Spare	VSELGT	
Bit	Bit		Bit Description						
VSELGT		VSEL Pin Gating 0 = Disabled 1 = Enabled							
Sleep_Mode		Sleep mode 0 = Low Iq mode when EN and VSEL low 1 = Force product in sleep mode (when EN and VSEL are low)							
DVSMODE		DVS transition mode selection 0 = Auto 1 = Forced PPWM							
C		Operating mode for MODE internal signal = High 0 = Auto 1 = Forced PPWM							
0 =		0 = A	Operating mode for MODE internal signal = Low ) = Auto I = Forced PPWM						

### **Table 22. LIMITS CONFIGURATION REGISTER**

Name: LIMCO	NF			Adress: 16h				
Type: RW			Default: See Register map					
Trigger: N/A								
D7	D6	D6 D5 I		D3	D2	D1	D0	
IPEAK[10]		TPWT	TPWTH[10]		FORCERST	RSTSTATUS	REARM	
Bit		Bit Description						
REARM		Rearming of device after TSD / ISHORT 0: No re–arming after TSD / ISHORT 1: Re–arming active after TSD / ISHORT with no reset of I <sup>2</sup> C registers: new power–up sequence is initiated with previously programmed I <sup>2</sup> C registers values						
(		Reset Indicator Bit 0: Must be written to 0 after register reset 1: Default (loaded after Registers reset)						
0:		Force Reset Bit 0: Default value. Self cleared to 0 1: Force reset of internal registers to default						
00 01 10		Thermal pre-Warnin 00 = 83°C 01 = 94°C 10 = 105°C 11 = 116°C	01 = 94°C 10 = 105°C					
00 01 10		00 = 5.2 A (for 3.5 A 01 = 5.8 A (for 4.0 A 10 = 6.2 A (for 4.5 A	nductor peak current settings 10 = 5.2 A (for 3.5 A output current) 11 = 5.8 A (for 4.0 A output current) 10 = 6.2 A (for 4.5 A output current) 11 = 6.8 A (for 5.0 A output current)					

#### APPLICATION INFORMATION

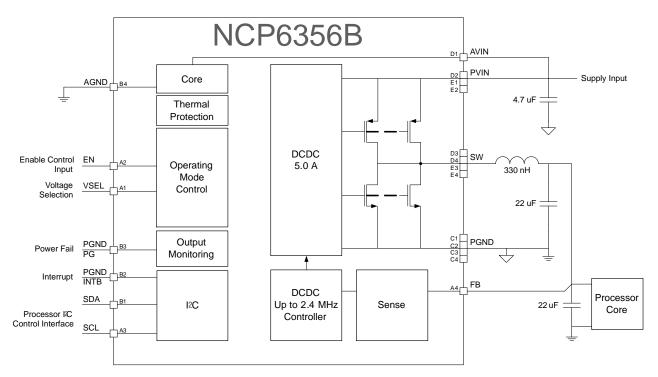


Figure 46. Typical Application Schematic

#### **Output Filter Considerations**

The output filter introduces a double pole in the system at a frequency of:

$$f_{LC} = \frac{1}{2 \cdot \pi \cdot \sqrt{L \cdot C}}$$
 (eq. 1)

The NCP6356B internal compensation network is optimized for a typical output filter comprising a 330 nH inductor and 47  $\mu$ F capacitor as described in the basic application schematic in Figure 46.

#### **Voltage Sensing Considerations**

In order to regulate the power supply rail, the NCP6356B must sense its output voltage. The IC can support two sensing methods:

- Normal sensing: The FB pin should be connected to the output capacitor positive terminal (voltage to regulate).
- Remote sensing: The power supply rail sense should be made close to the system powered by the NCP6356B.
   The voltage to the system is more accurate, since the PCB line impedance voltage drop is within the regulation loop. In this case, we recommend connecting the FB pin to the system decoupling capacitor positive terminal.

# Components Selection Inductor Selection

The inductance of the inductor is chosen such that the peak–to–peak ripple current  $I_{L\_PP}$  is approximately 20% to 50% of the maximum output current  $I_{OUT\_MAX}$ . This provides the best trade–off between transient response and output ripple. The inductance corresponding to a given current ripple is:

$$L = \frac{\left(V_{\text{IN}} - V_{\text{OUT}}\right) \cdot V_{\text{OUT}}}{V_{\text{IN}} \cdot f_{\text{SW}} \cdot I_{\text{L PP}}}$$
 (eq. 2)

The selected inductor must have a saturation current rating higher than the maximum peak current which is calculated by:

$$I_{L\_MAX} = I_{OUT\_MAX} + \frac{I_{L\_PP}}{2}$$
 (eq. 3)

The inductor must also have a high enough current rating to avoid self-heating. A low DCR is therefore preferred. Refer to Table 23 for recommended inductors.

**Table 23. INDUCTOR SELECTION** 

Supplier	Part #	Value (μΗ)	Size (mm) (L x I x T) (mm)	Saturation Current Max (A)	DCR Max at 25°C (mΩ)
Cyntec	PIFE20161B-R33MS-11	0.33	2.0 x 1.6 x 1.2	4.0	33
Cyntec	PIFE25201B-R33MS-11	0.33	2.5 x 2.0 x 1.2	5.2	17
Cyntec	PIFE32251B-R33MS-11	0.33	3.2 x 2.5 x 1.2	6.5	14
TOKO	DFE252012F-H-R33M	0.33	2.5 x 2.0 x 1.2	5.1	13
TOKO	DFE201612E-H-R33M	0.33	2.0 x 1.6 x 1.2	4.8	21
TOKO	FDSD0412-H-R33M	0.33	4.2 x 4.2 x 1.2	7.5	19
TDK	VLS252012HBX-R33M	0.33	2.5 x 2.0 x 1.2	5.3	25
TDK	SPM5030T-R35M	0.35	7.1 x 6.5 x 3.0	14.9	4

#### **Output Capacitor Selection**

The output capacitor selection is determined by output voltage ripple and load transient response requirement. For high transient load performance a high output capacitor value must be used. For a given peak—to—peak ripple current  $I_{L\_PP}$  in the inductor of the output filter, the output voltage ripple across the output capacitor is the sum of three components as shown below.

$$V_{OUT\_PP} \approx V_{OUT\_PP(C)} + V_{OUT\_PP(ESR)} + V_{OUT\_PP(ESL)}$$
, (eq. 4)

With:

$$V_{OUT\_PP(C)} = \frac{I_{L\_PP}}{8 \cdot C \cdot f_{SW}},$$
 (eq. 5)

$$V_{OUT\_PP(ESR)} = I_{L\_PP} \cdot ESR$$
 (eq. 6)

$$V_{OUT\_PP(ESL)} = \frac{ESL}{ESL + L} \cdot V_{IN}$$
 (eq. 7)

Where the peak-to-peak ripple current is given by

$$I_{L\_PP} = \frac{\left(V_{IN} - V_{OUT}\right) \cdot V_{OUT}}{V_{IN} \cdot f_{SW} \cdot L}$$
 (eq. 8)

In applications with all ceramic output capacitors, the main ripple component of the output ripple is  $V_{OUT\_PP(C)}$ . The minimum output capacitance can be calculated based on a given output ripple requirement  $V_{OUT\_PP}$  in PPWM operation mode.

$$C_{MIN} = \frac{I_{L\_PP}}{8 \cdot V_{OUT\_PP} \cdot f_{SW}}$$
 (eq. 9)

#### **Input Capacitor Selection**

One of the input capacitor selection requirements is the input voltage ripple. To minimize the input voltage ripple and get better decoupling at the input power supply rail, a ceramic capacitor is recommended due to low ESR and ESL. The minimum input capacitance with respect to the input ripple voltage  $V_{\mbox{\scriptsize IN\_PP}}$  is

$$C_{IN\_MIN} = \frac{I_{OUT\_MAX} \cdot (D - D^2)}{V_{IN\_PP} \cdot f_{SW}}$$
 (eq. 10)

where

$$D = \frac{V_{OUT}}{V_{IN}}$$
 (eq. 11)

In addition, the input capacitor must be able to absorb the input current, which has a RMS value of

$$I_{\text{IN\_RMS}} = I_{\text{OUT\_MAX}} \cdot \sqrt{D - D^2}$$
 (eq. 12)

The input capacitor also must be sufficient to protect the device from over voltage spikes, and a 4.7  $\mu$ F capacitor or greater is required. The input capacitor should be located as close as possible to the IC. All PGND pins must be connected together to the ground terminal of the input cap which then must be connected to the ground plane. All PVIN pins must be connected together to the Vbat terminal of the input cap which then connects to the Vbat plane.

#### **Power Capability**

The NCP6356B's power capability is driven by the difference in temperature between the junction  $(T_J)$  and ambient  $(T_A)$ , the junction–to–ambient thermal resistance  $(R_{\theta JA})$ , and the on–chip power dissipation  $(P_{IC})$ .

The on–chip power dissipation  $P_{IC}$  can be determined as  $P_{IC}$  =  $P_T - P_L$  with the total power losses  $P_T$  being

$$P_T = V_{OUT} \times I_{OUT} \times \left(\frac{1}{\eta} - 1\right)$$
 (eq. 13)

where  $\eta$  is the efficiency and  $P_L$  the simplified inductor power losses  $P_L = I_{LOAD}{}^2\,x$  DCR.

Now the junction temperature  $T_J$  can easily be calculated as  $T_J = R_{\theta JA} \ x \ P_{IC} + T_A$ .

Please note that the  $T_J$  should stay within the recommended operating conditions.

The  $R_{\theta JA}$  is a function of the PCB layout (number of layers and copper and PCB size). For example, the NCP6356B mounted on the EVB has a  $R_{\theta JA}$  about 55°C/W.

#### **Layout Considerations**

#### **Electrical Rules**

Good electrical layout is key to proper operation, high efficiency, and noise reduction. Electrical layout guidelines are:

- Use wide and short traces for power paths (such as PVIN, VOUT, SW, and PGND) to reduce parasitic inductance and high-frequency loop area. It is also good for efficiency improvement.
- The device should be well decoupled by input capacitor and the input loop area should be as small as possible to reduce parasitic inductance, input voltage spike, and noise emission.
- SW track should be wide and short to reduce losses and noise radiation.
- It is recommended to have separated ground planes for PGND and AGND and connect the two planes at one point. Try to avoid overlap of input ground loop and output ground loop to prevent noise impact on output regulation.
- Arrange a "quiet" path for output voltage sense, and make it surrounded by a ground plane.

#### **Thermal Rules**

Good PCB layout improves the thermal performance and thus allows for high power dissipation even with a small IC package. Thermal layout guidelines are:

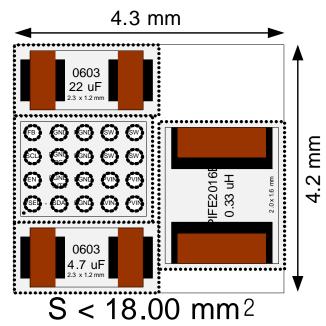


Figure 47. Placement Recommendation

- A four or more layers PCB board with solid ground planes is preferred for better heat dissipation.
- Use multiple vias around the IC to connect the inner ground layers to reduce thermal impedance.
- Use a large and thick copper area especially in the top layer for good thermal conduction and radiation.
- Use two layers or more for the high current paths (PVIN, PGND, SW) in order to split current into different paths and limit PCB copper self—heating.

#### **Component Placement**

- Input capacitor placed as close as possible to the IC.
- PVIN directly connected to Cin input capacitor, and then connected to the Vin plane. Local mini planes used on the top layer (green) and the layer just below the top layer (yellow) with laser vias.
- **AVIN** connected to the Vin plane just after the capacitor.
- **AGND** directly connected to the GND plane.
- **PGND** directly connected to Cin input capacitor, and then connected to the GND plane: Local mini planes used on the top layer (green) and the layer just below the top layer (yellow) with laser vias.
- **SW** connected to the Lout inductor with local mini planes used on the top layer (green) and the layer just below the top layer (yellow) with laser vias.

(See Figures 47 and 48 for examples)

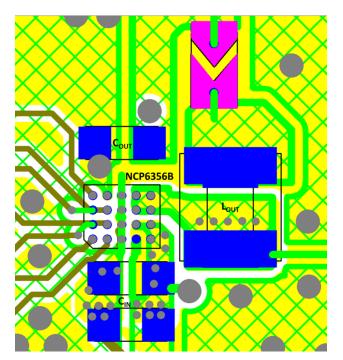


Figure 48. Demo Board Example

#### Legend:

Green: top layer planes and wires

Yellow: layer1 plane and wires (just below top layer)

Big grey circles: normal vias

Small gray circles: top to layer1 vias

#### **ORDERING INFORMATION**

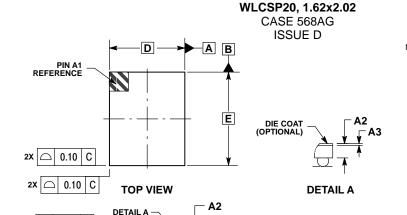
Device	Marking	Configuration	Package	Shipping <sup>†</sup>
NCP6356BFCCT1G	6356B	5.0 A 1.15 V ON		
NCP6356BSFCCT1G	6356BS	4.0 A 0.95 V ON		
NCP6356BSNFCCT1G	6356BN	4.0 A 1.20 V ON	WLCSP20 2.02 x 1.62 mm (Pb-Free)	3000 / Tape & Reel
NCP6356BVFCCT1G	6356BV	5.0 A 1.00 V ON		
NCP6356BWFCCT1G	6356BW	5.0 A 0.80 V ON		

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **Demo Board Available:**

The NCP6356BGEVB/D evaluation board that configures the device in typical application to supply constant voltage.

#### PACKAGE DIMENSIONS

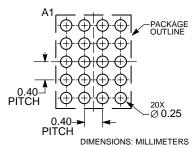


#### NOTES:

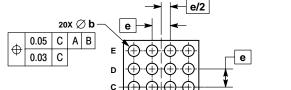
- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS.
  COPLANARITY APPLIES TO THE SPHERICAL
  CROWNS OF THE SOLDER BALLS.

ONOTHING OF THE COLD						
	MILLIMETERS					
DIM	MIN MAX					
Α		0.60				
A1	0.17	0.23				
A2	0.33	0.39				
A3	0.02	0.04				
b	0.24	0.28				
D	1.62 BSC					
Е	2.02 BSC					
е	0.40 BSC					





\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



В

SIDE VIEW

0.10 С

Δ1

0.05 С

NOTE 3

**BOTTOM VIEW** 

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